

International
IR Rectifier

PD- 92006A

SMPS MOSFET

IRF830AS/L

HEXFET® Power MOSFET

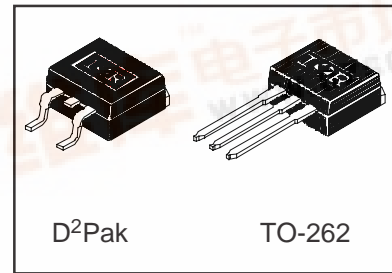
Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptable Power Supply
- High Speed Power Switching

V_{DSS}	R_{DS(on)} max	I_D
500V	1.40Ω	5.0A

Benefits

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective Coss specified (See AN 1001)



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V ^⑥	5.0	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V ^⑥	3.2	
I _{DM}	Pulsed Drain Current ^{①⑥}	20	
P _D @ T _A = 25°C	Power Dissipation	3.1	W
P _D @ T _C = 25°C	Power Dissipation	74	
	Linear Derating Factor	0.59	W/°C
V _{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ^{③⑥}	5.3	V/ns
T _J	Operating Junction and	-55 to + 150	
T _{STG}	Storage Temperature Range		°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Typical SMPS Topologies:

- Two Transistor Forward
- Half Bridge and Full Bridge

Notes ^① through ^⑤ are on page 10

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.60	—		$V/^\circ\text{C}$ Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	1.4	Ω	$V_{GS} = 10V, I_D = 3.0A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25 250	μA	$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	2.8	—	—	S	$V_{DS} = 50V, I_D = 3.0A$ ⑥
Q_g	Total Gate Charge	—	—	24	nC	$I_D = 5.0A$ $V_{DS} = 400V$ $V_{GS} = 10V$, See Fig. 6 and 13 ④⑥
Q_{gs}	Gate-to-Source Charge	—	—	6.3		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	11	ns	$V_{DD} = 250V$ $I_D = 5.0A$ $R_G = 14\Omega$ $R_D = 49\Omega$, See Fig. 10 ④⑥
$t_{d(on)}$	Turn-On Delay Time	—	10	—		
t_r	Rise Time	—	21	—		
$t_{d(off)}$	Turn-Off Delay Time	—	21	—		
t_f	Fall Time	—	15	—		
C_{iss}	Input Capacitance	—	620	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0\text{MHz}$, See Fig. 5 $V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 400V, f = 1.0\text{MHz}$ $V_{GS} = 0V, V_{DS} = 0V$ to $400V$ ⑤⑥
C_{oss}	Output Capacitance	—	93	—		
C_{rss}	Reverse Transfer Capacitance	—	4.3	—		
C_{oss}	Output Capacitance	—	886	—		
C_{oss}	Output Capacitance	—	27	—		
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	39	—		

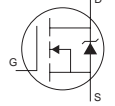
Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②⑥	—	230	mJ
I_{AR}	Avalanche Current①⑥	—	5.0	A
E_{AR}	Repetitive Avalanche Energy①	—	7.4	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.7	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)*	—	40	

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	5.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	20		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 5.0A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	430	650	ns	$T_J = 25^\circ\text{C}, I_F = 5.0A$
Q_{rr}	Reverse Recovery Charge	—	2.0	3.0	μC	$di/dt = 100A/\mu s$ ④⑥
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

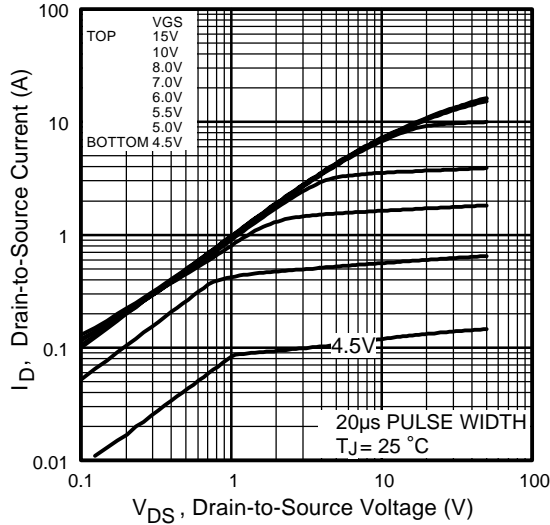


Fig 1. Typical Output Characteristics

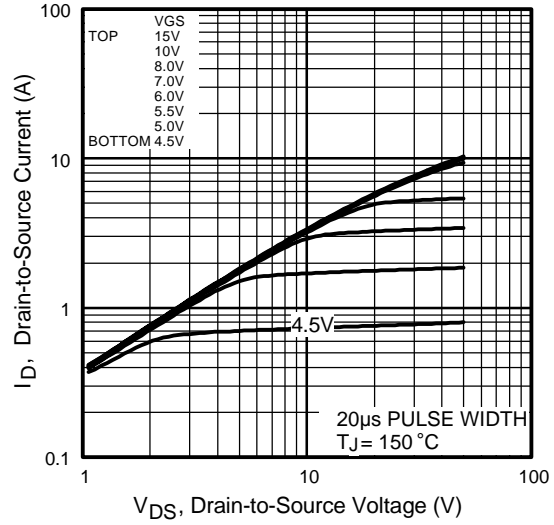


Fig 2. Typical Output Characteristics

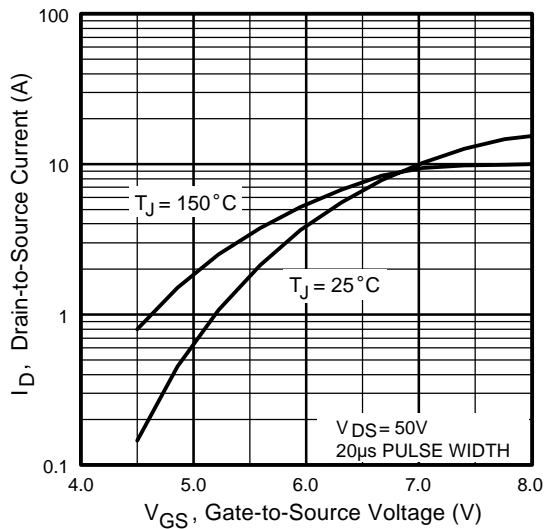


Fig 3. Typical Transfer Characteristics

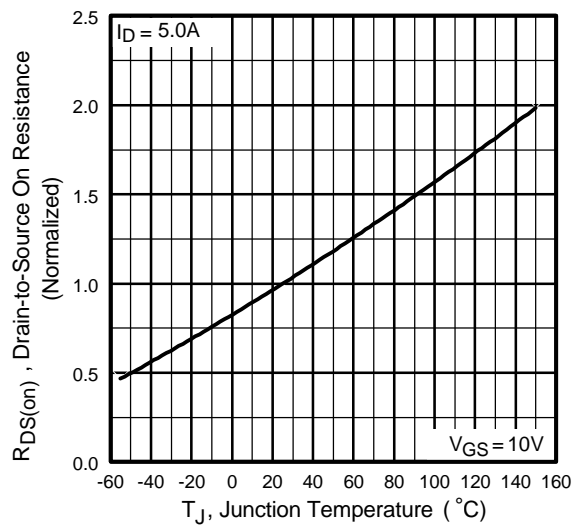


Fig 4. Normalized On-Resistance Vs. Temperature

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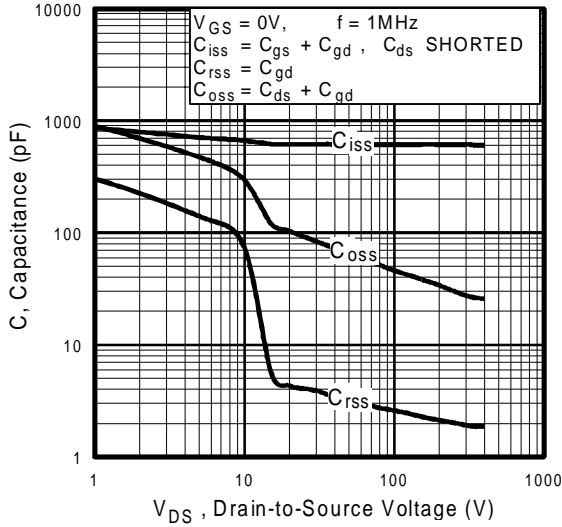


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

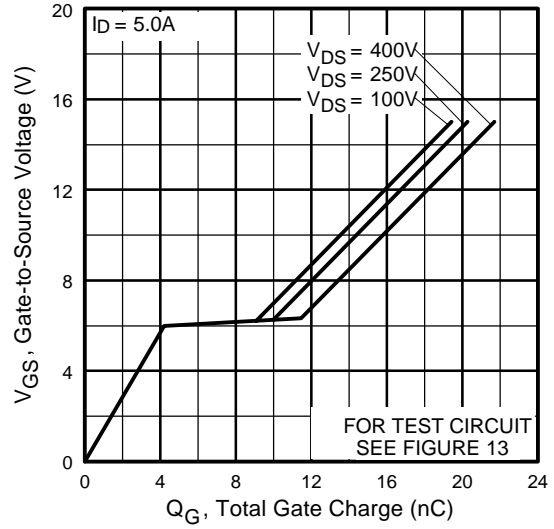


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

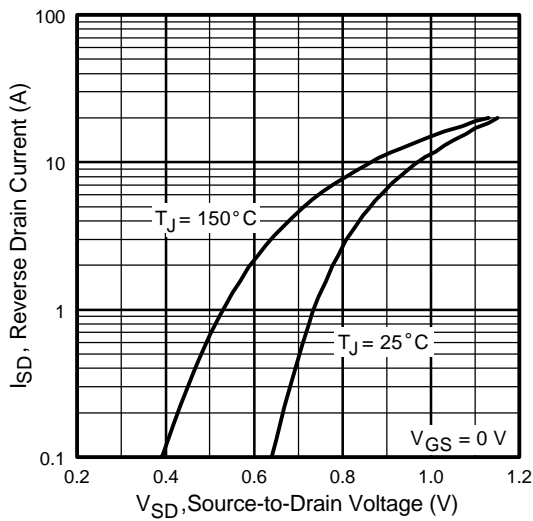


Fig 7. Typical Source-Drain Diode Forward Voltage

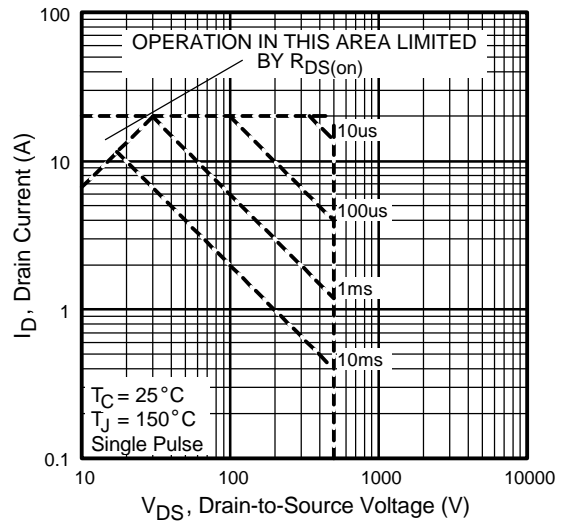


Fig 8. Maximum Safe Operating Area

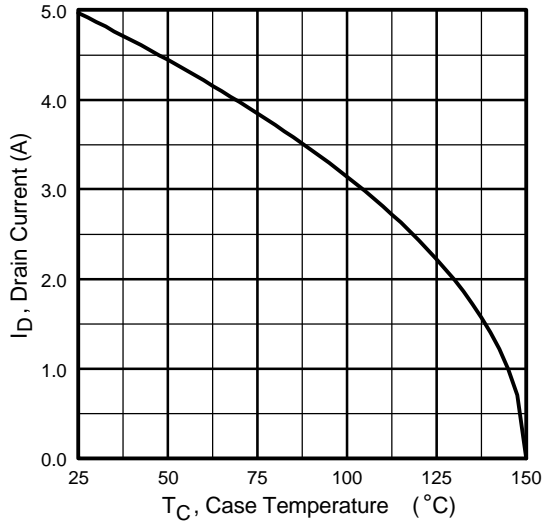


Fig 9. Maximum Drain Current Vs. Case Temperature

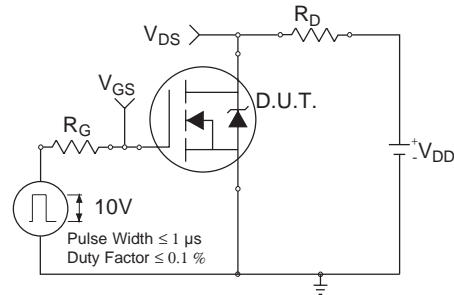


Fig 10a. Switching Time Test Circuit

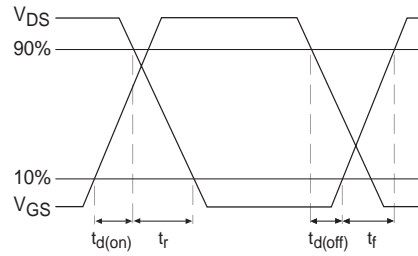


Fig 10b. Switching Time Waveforms

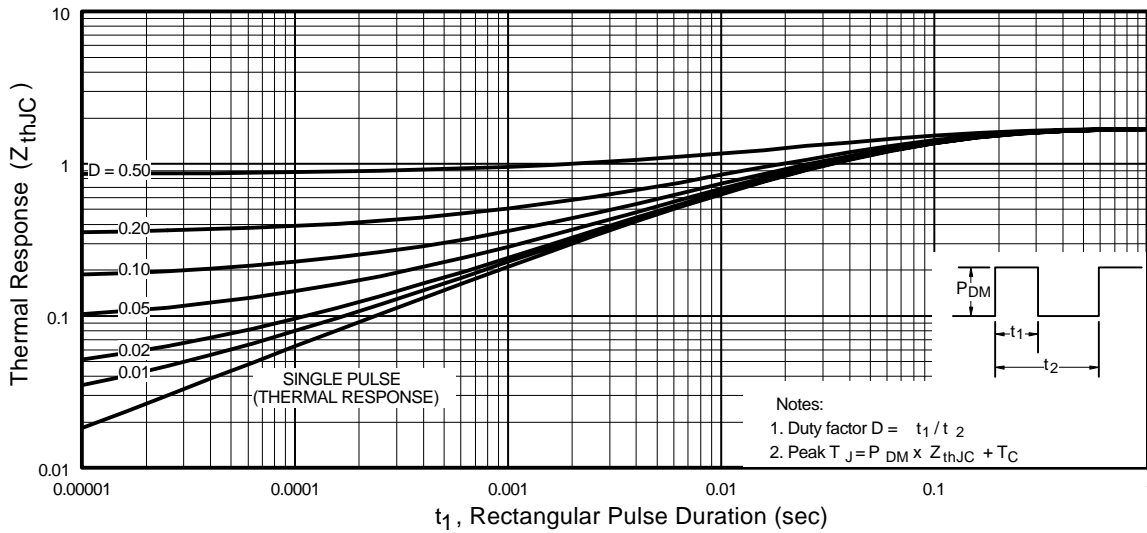


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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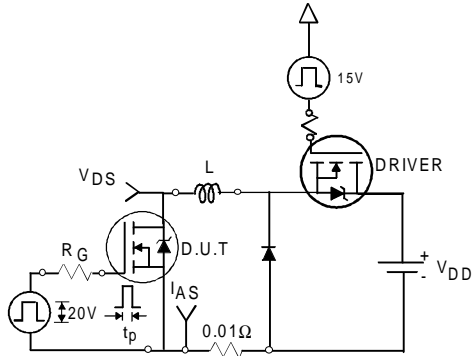


Fig 12a. Unclamped Inductive Test Circuit

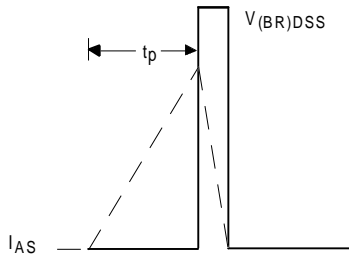


Fig 12b. Unclamped Inductive Waveforms

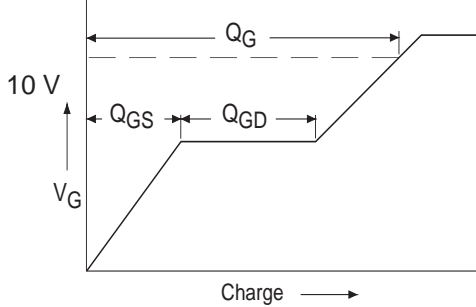


Fig 13a. Basic Gate Charge Waveform

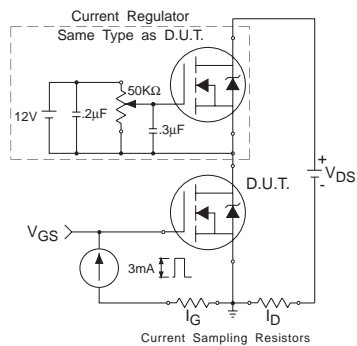


Fig 13b. Gate Charge Test Circuit

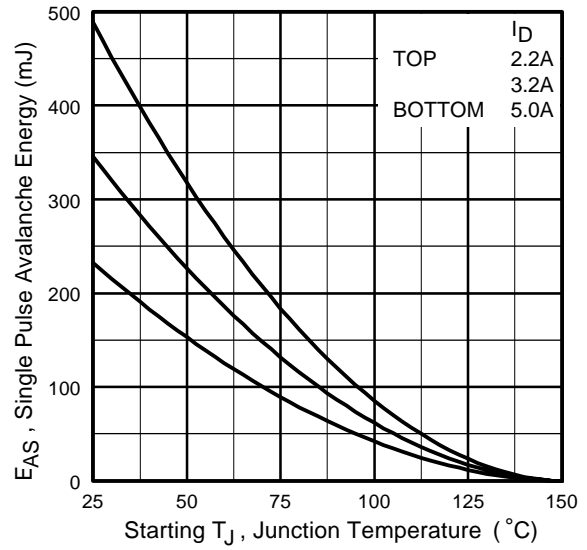


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

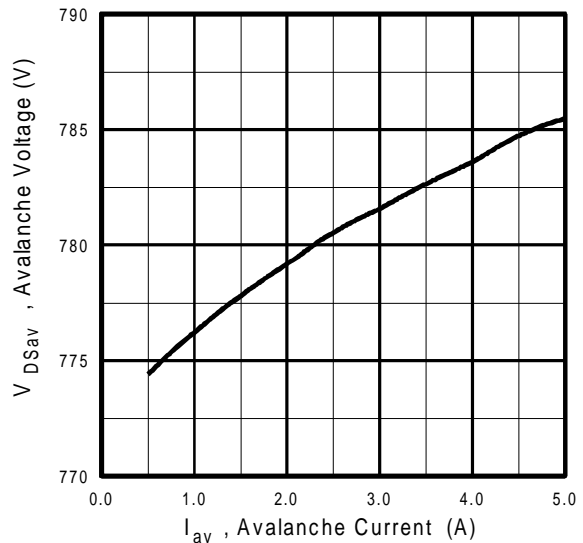
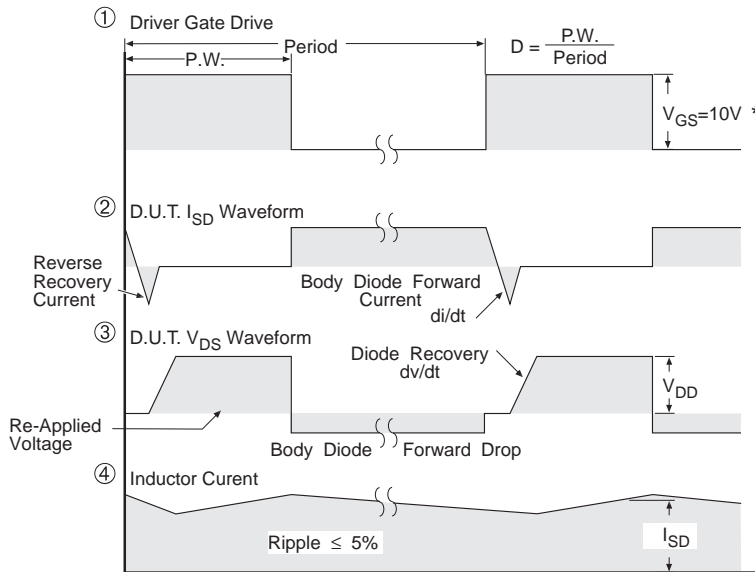
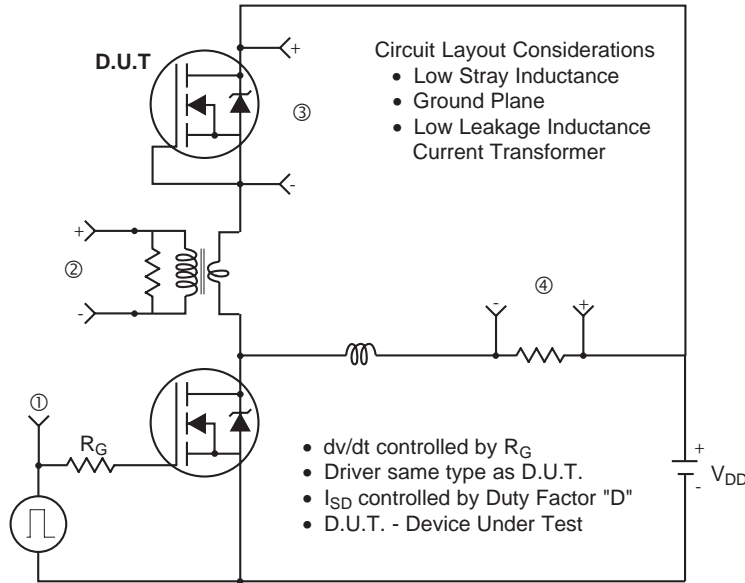


Fig 12d. Typical Drain-to-Source Voltage Vs. Avalanche Current

Peak Diode Recovery dv/dt Test Circuit



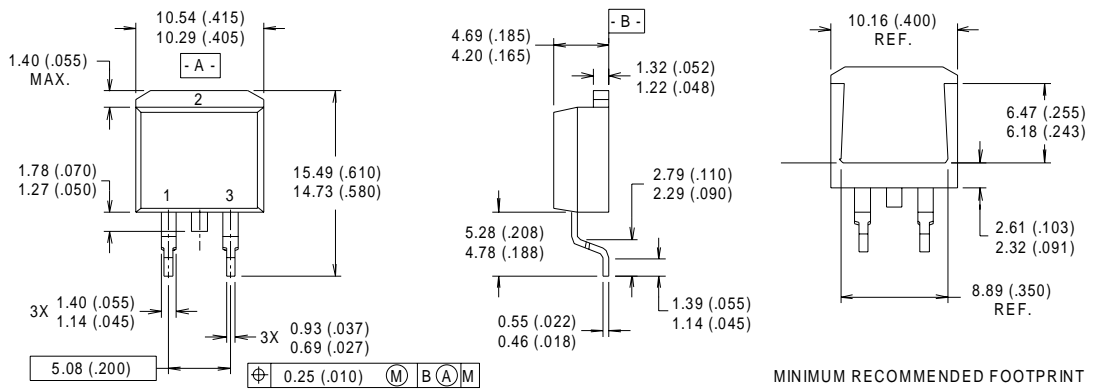
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFET

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D²Pak Package Outline



NOTES:

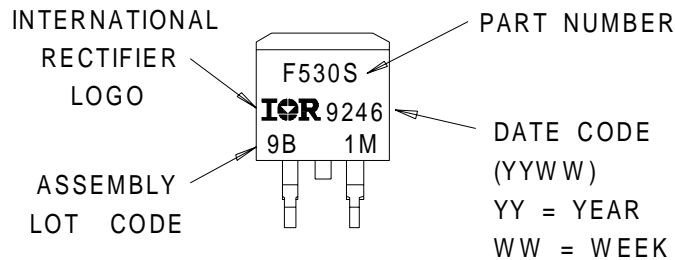
- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

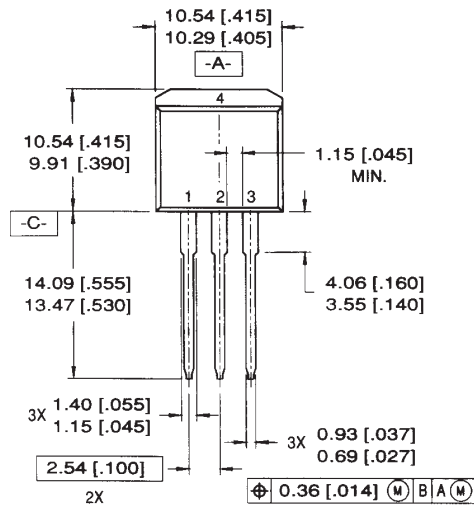
Part Marking Information

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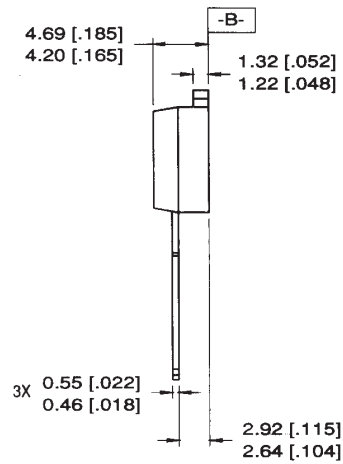
Package Outline

TO-262 Outline



LEAD ASSIGNMENTS

1 = GATE 3 = SOURCE
 2 = DRAIN 4 = DRAIN



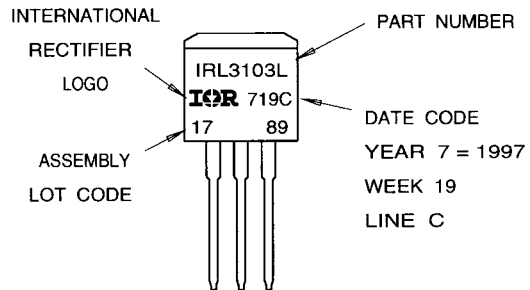
NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

Part Marking Information

TO-262

EXAMPLE: THIS IS AN IRL3103L
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"

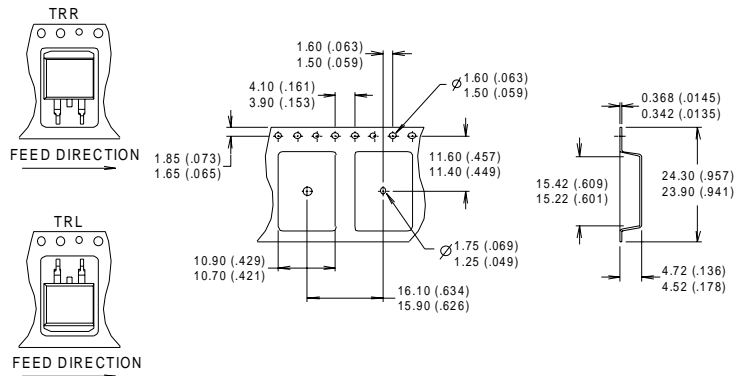


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Tape & Reel Information

D²Pak



- NOTES :
1. CONFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION MEASURED @ HUB.
 4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 18\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 5.0\text{A}$. (See Figure 12)
- ③ $I_{SD} \leq 5.0\text{A}$, $di/dt \leq 370\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}
- ⑥ Uses IRF830A data and test conditions

* When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

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Data and specifications subject to change without notice. 5/00